

To all our customers

Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.)

Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

CR12AM

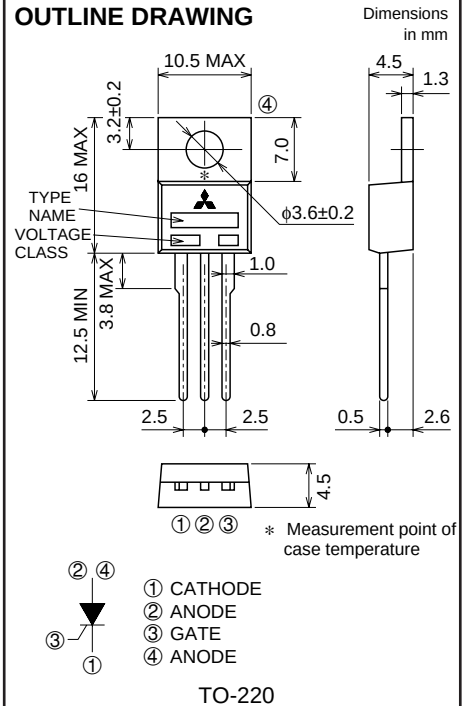
MEDIUM POWER USE
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

CR12AM



- I_T (AV) 12A
- V_{DRM} 400V/600V
- I_{GT} 30mA

OUTLINE DRAWING



APPLICATION

Switching mode power supply, ECR, motor control

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8	12	
V_{RRM}	Repetitive peak reverse voltage	400	600	V
V_{RSM}	Non-repetitive peak reverse voltage	500	720	V
V_R (DC)	DC reverse voltage	320	480	V
V_{DRM}	Repetitive peak off-state voltage	400	600	V
V_D (DC)	DC off-state	320	480	V

Symbol	Parameter	Conditions	Ratings	Unit
I_T (RMS)	RMS on-state current		18.8	A
I_T (AV)	Average on-state current	Commercial frequency, sine half wave, 180° conduction, $T_c=91^\circ\text{C}$	12.0	A
I_{TSM}	Surge on-state current	60Hz sine half wave 1 full cycle, peak value, non-repetitive	360	A
I^2_t	I^2_t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	544	A ² s
PGM	Peak gate power dissipation		5	W
PG (AV)	Average gate power dissipation		0.5	W
V_{FGM}	Peak gate forward voltage		6	V
V_{RGM}	Peak gate reverse voltage		10	V
I_{FGM}	Peak gate forward current		2	A
T_j	Junction temperature		-40 ~ +125	°C
T_{stg}	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	2.0	g

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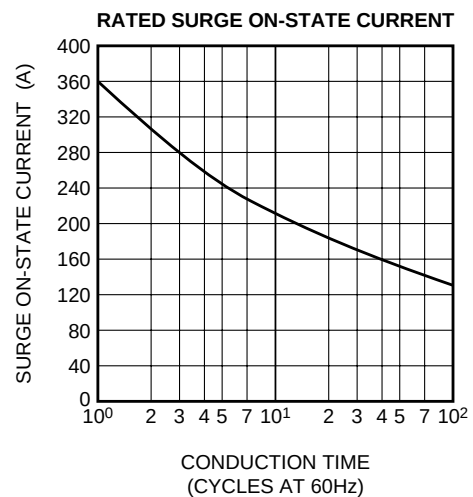
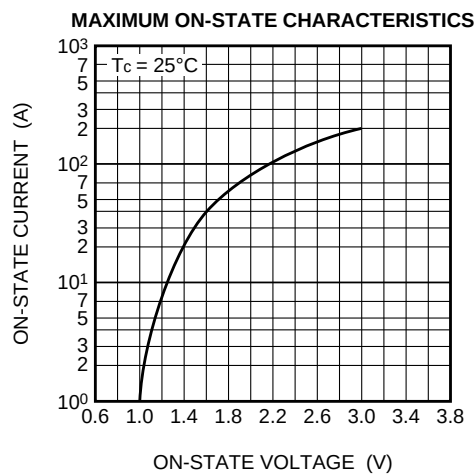
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ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IRRM	Repetitive peak reverse current	$T_J=125^{\circ}\text{C}$, V_{RRM} applied	—	—	2.0	mA
IDRM	Repetitive peak off-state current	$T_J=125^{\circ}\text{C}$, V_{DRM} applied	—	—	2.0	mA
V_{TM}	On-state voltage	$T_c=25^{\circ}\text{C}$, $I_{TM}=40\text{A}$,	—	—	1.6	V
V_{GT}	Gate trigger voltage	$T_J=25^{\circ}\text{C}$, $V_D=6\text{V}$, $I_T=1\text{A}$	—	—	1.5	V
V_{GD}	Gate non-trigger voltage	$T_J=125^{\circ}\text{C}$, $V_D=1/2V_{DRM}$	0.2	—	—	V
I_{GT}	Gate trigger current	$T_J=25^{\circ}\text{C}$, $V_D=6\text{V}$, $I_T=1\text{A}$	—	—	30	mA
I_H	Holding current	$T_J=25^{\circ}\text{C}$, $V_D=12\text{V}$	—	15	—	mA
$R_{th(j-c)}$	Thermal resistance	Junction to case *1	—	—	1.2	$^{\circ}\text{C/W}$

*1. The contact thermal resistance $R_{th(j-c)}$ is 1.0°C/W with greased.

PERFORMANCE CURVES

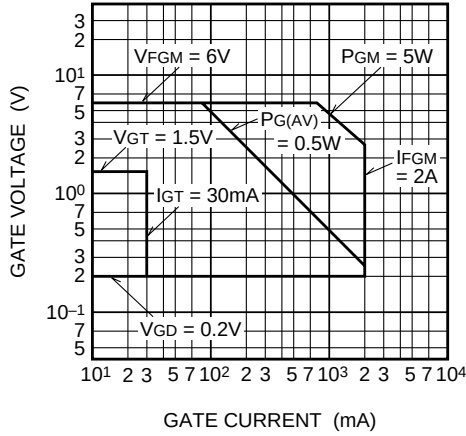


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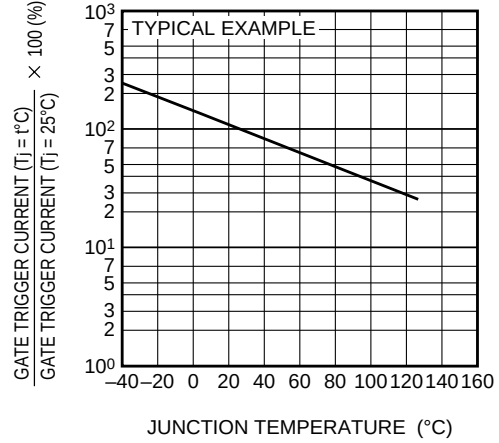
MEDIUM POWER USE

NON-INSULATED TYPE, GLASS PASSIVATION TYPE

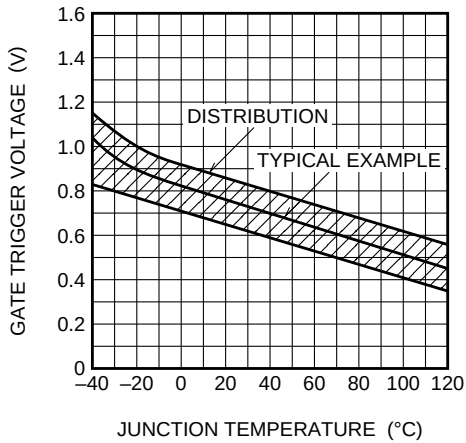
GATE CHARACTERISTICS



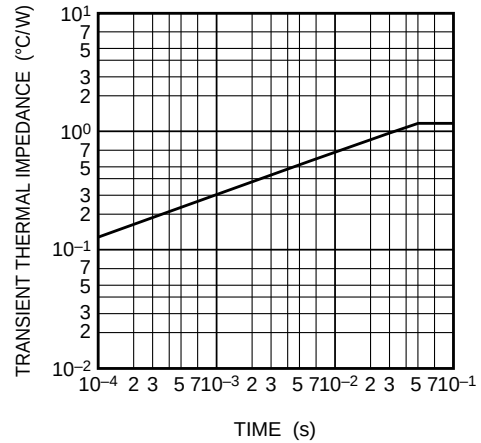
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



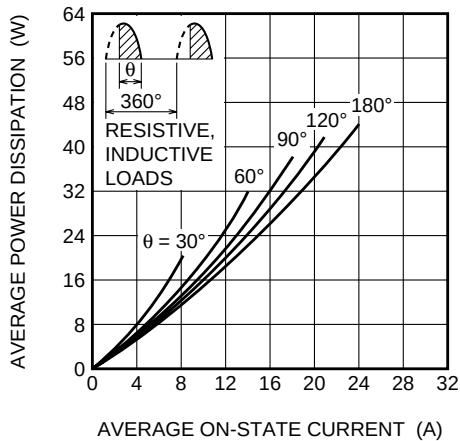
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



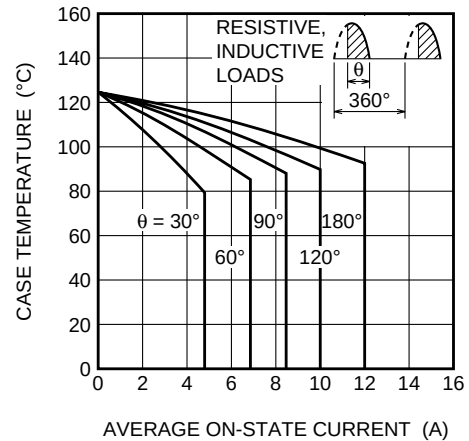
MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)



MAXIMUM AVERAGE POWER DISSIPATION (SINGLE-PHASE HALF WAVE)



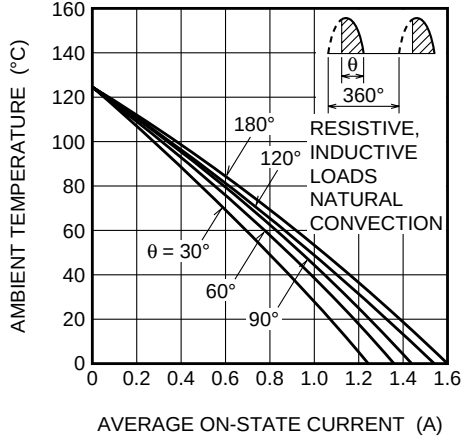
ALLOWABLE CASE TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



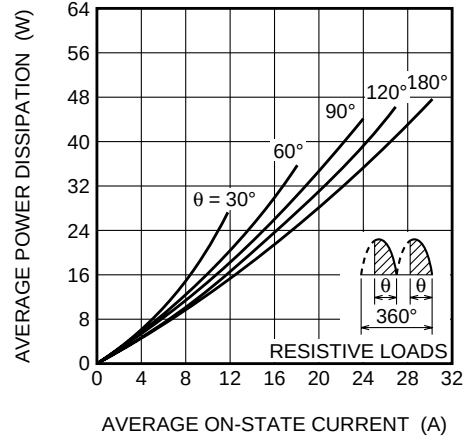
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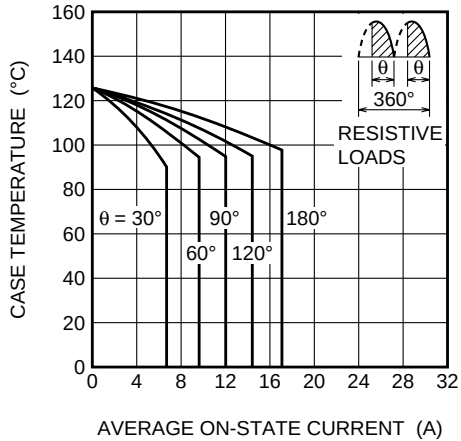
ALLOWABLE AMBIENT TEMPERATURE VS.
AVERAGE ON-STATE CURRENT
(SINGLE-PHASE HALF WAVE)



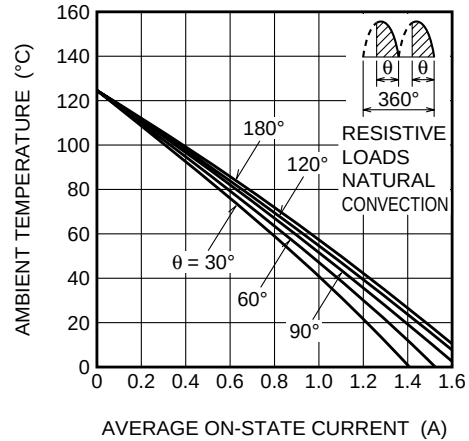
MAXIMUM AVERAGE POWER DISSIPATION
(SINGLE-PHASE FULL WAVE)



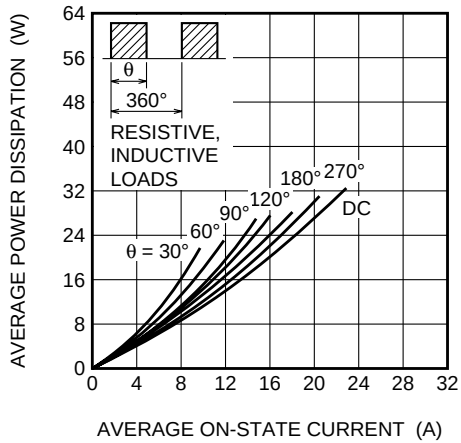
ALLOWABLE CASE TEMPERATURE VS.
AVERAGE ON-STATE CURRENT
(SINGLE-PHASE FULL WAVE)



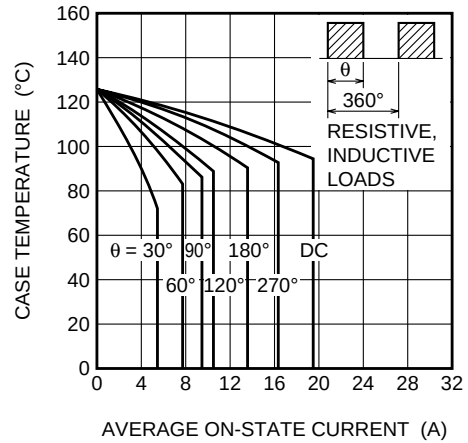
ALLOWABLE AMBIENT TEMPERATURE VS.
AVERAGE ON-STATE CURRENT
(SINGLE-PHASE FULL WAVE)



MAXIMUM AVERAGE POWER DISSIPATION
(RECTANGULAR WAVE)



ALLOWABLE CASE TEMPERATURE VS.
AVERAGE ON-STATE CURRENT
(RECTANGULAR WAVE)

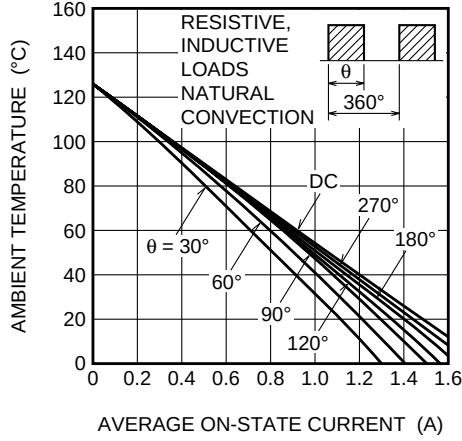


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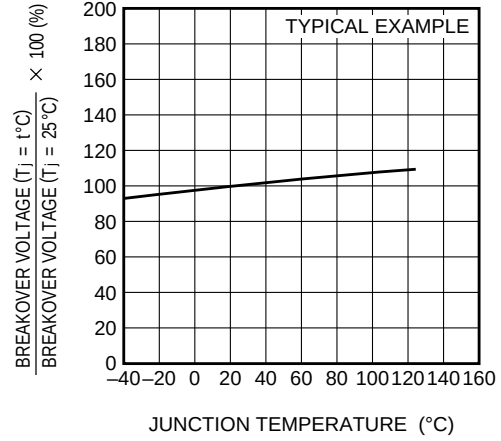
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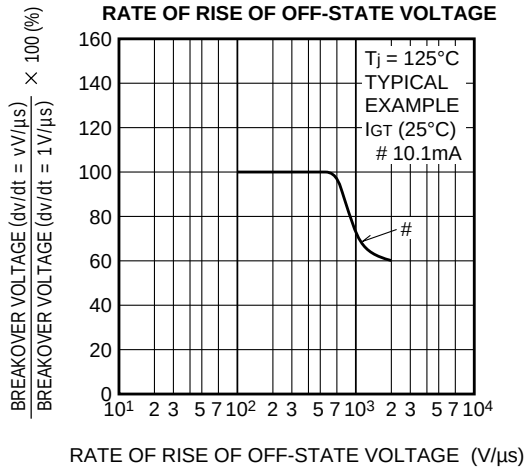
**ALLOWABLE AMBIENT TEMPERATURE VS.
AVERAGE ON-STATE CURRENT
(RECTANGULAR WAVE)**



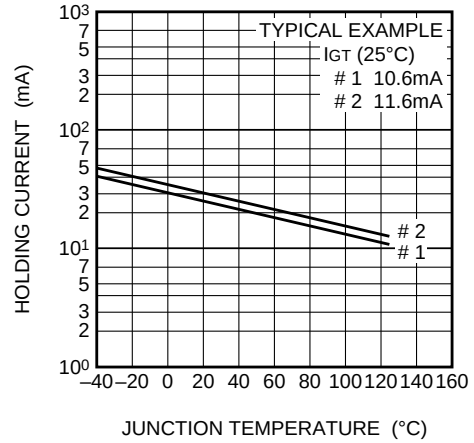
**BREAKEOVER VOLTAGE VS.
JUNCTION TEMPERATURE**



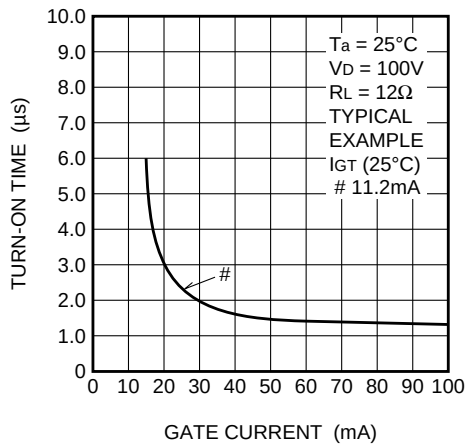
**BREAKEOVER VOLTAGE VS.
RATE OF RISE OF OFF-STATE VOLTAGE**



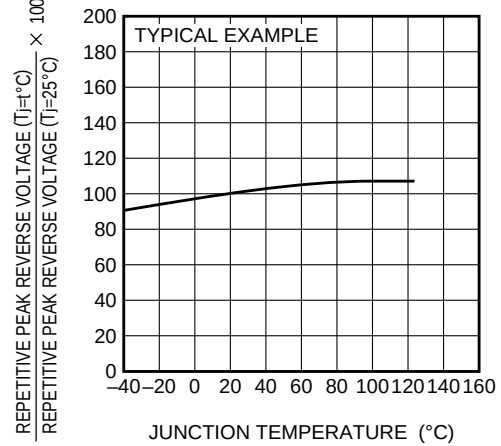
**HOLDING CURRENT VS.
JUNCTION TEMPERATURE**



TURN-ON TIME VS. GATE CURRENT



**REPETITIVE PEAK REVERSE VOLTAGE VS.
JUNCTION TEMPERATURE**



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